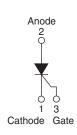


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Vishay Semiconductors

Thyristor, Surface Mount, Phase Control SCR, 16 A





PRODUCT SUMMARY					
TO-263AB (D ² PAK)					
Single SCR					
16 A					
800 V, 1200 V					
1.25 V					
45 mA					
- 40 to 125 °C					

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC-JESD47
- Material categorization:
 For definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5					
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	A				
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0					

Note

T_A = 55 °C, T_J = 125 °C, footprint 300 mm²

PARAMETER	TEST CONDITIONS	VALUES	UNITS
I _{T(AV)}	Sinusoidal waveform	16	Δ.
I _{RMS}		25	Α
V _{RRM} /V _{DRM}		800 to 1200	V
I _{TSM}		350	A
V _T	16 A, T _J = 25 °C	1.25	V
dV/dt		500	V/µs
dl/dt		150	A/µs
TJ		- 40 to 125	°C

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA
VS-25TTS08SPbF	800	800	10
VS-25TTS12SPbF	1200	1200	10



PARAMETER	SYMBOL	T	CT CONDITIONS	VAL	UES	LINUTO				
PARAMETER	SYMBOL	TEST CONDITIONS			MAX.	UNITS				
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° (conduction half sine wave	1	6					
Maximum RMS on-state current	I _{RMS}			2	5	Α				
Maximum peak, one-cycle,	_	10 ms sine pulse,	rated V _{RRM} applied	30	00	^				
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50					
Maximum I ² t for fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	4	50	A ² s				
Maximum i-t for fusing	1-1	10 ms sine pulse,	no voltage reapplied	6	30	A-5				
Maximum $I^2\sqrt{t}$ for fusing	I²√t	t = 0.1 ms to 10 m	t = 0.1 ms to 10 ms, no voltage reapplied			A²√s				
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C		1.	25	V				
On-state slope resistance	r _t	T _{.1} = 125 °C		12	2.0	mΩ				
Threshold voltage	V _{T(TO)}	- IJ = 125 C		1	.0	V				
Maximum reverse and direct leakage current	1 /1	T _J = 25 °C	V - Patad V A/	0	.5					
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	$V_R = Rated V_{RRM}/V_{DRM}$		1	0					
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $I_J = 25$ °C	-	150	mA				
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C		Anode supply = 6 V, resistive load, T _J = 25 °C		Anode supply = 6 V, resistive load, T _J = 25 °C		20	00	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = Open$			00	V/µs				
Maximum rate of rise of turned-on current	dl/dt	Ü			50	A/µs				

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
		Anode supply = 6 V, resistive load, T_J = - 10 °C	60	
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	45	mA
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	
		Anode supply = 6 V, resistive load, T_J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V Detect value	0.25	
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	2.0	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9	
Typical reverse recovery time	t _{rr}	T _{.I} = 125 °C	4	μs
Typical turn-off time	t _q	1J = 125	110	

THERMAL AND MECHANICAL	THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		- 40 to 125	°C			
Soldering temperature	T _S	For 10 s (1.6 mm from case)	260				
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.1	°C/W			
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/VV			
Approximate weight			2	g			
Approximate weight			0.07	oz.			
Madding daving		Case style D ² PAK (SMD-220)	25TT	S08S			
Marking device		Case style D-FAN (SIVID-220)	25TT	S12S			

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

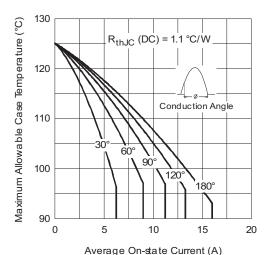
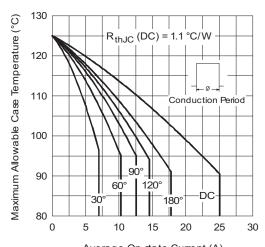


Fig. 1 - Current Rating Characteristics



Average On-state Current (A) Fig. 2 - Current Rating Characteristics

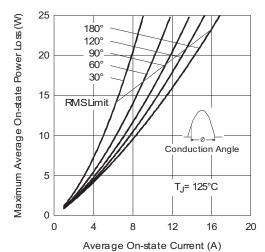
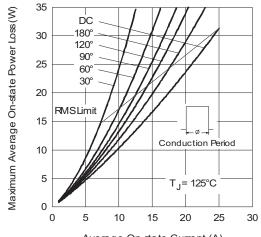


Fig. 3 - On-State Power Loss Characteristics



Average On-state Current (A) Fig. 4 - On-State Power Loss Characteristics



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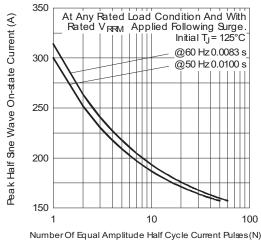


Fig. 5 - Maximum Non-Repetitive Surge Current

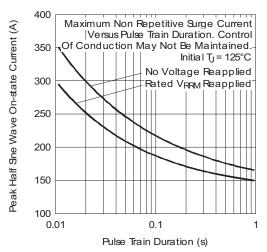


Fig. 6 - Maximum Non-Repetitive Surge Current

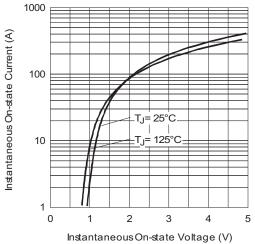


Fig. 7 - On-State Voltage Drop Characteristics

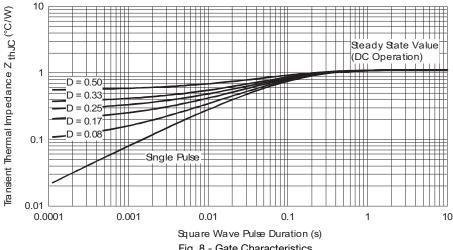


Fig. 8 - Gate Characteristics

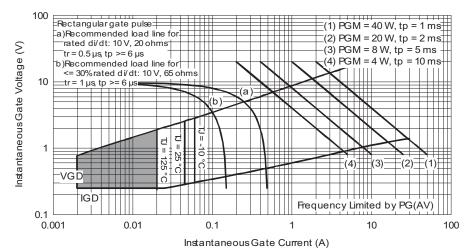


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code	VS-	25	Т	Т	S	12	S	TRL	PbF
	1	2	3	4	5	6	7	8	9

- Vishay Semiconductors product
- Current rating (25 = 25 A)
- Circuit configuration:
 - T = Single thyristor
- Package: T = TO-220AC
- 5 Type of silicon:
- S = Standard recovery rectifier
- 08 = 800 V6 Voltage rating: Voltage code x 100 = V_{RRM} 12 = 1200 V
- 7 $S = TO-220 D^2PAK (SMD-220) version$
- None = Tube
 - TRL = Tape and reel (left oriented)
 - TRR = Tape and reel (right oriented)
- 9 PbF = Lead (Pb)-free

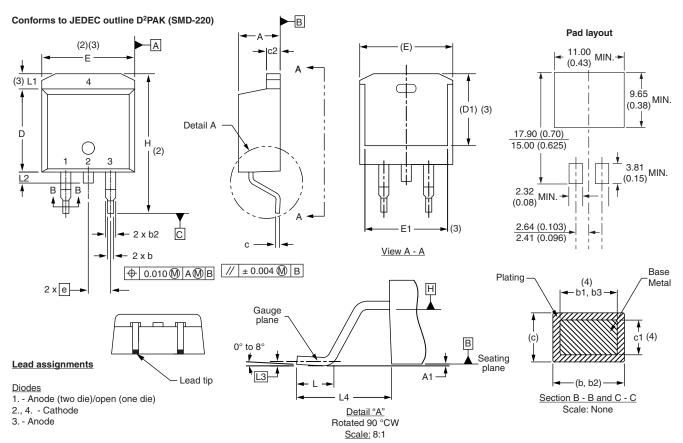
ORDERING INFORMATI	ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-25TTS08SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS08STRRPbF	800	800	13" diameter reel				
VS-25TTS08STRLPbF	800	800	13" diameter reel				
VS-25TTS12SPbF	50	1000	Antistatic plastic tubes				
VS-25TTS12STRRPbF	800	800	13" diameter reel				
VS-25TTS12STRLPbF	800	800	13" diameter reel				

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95046</u>				
Part marking information	www.vishay.com/doc?95054			
Packaging information	www.vishay.com/doc?95032			



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MIN. MAX.		MAX.	NOTES
Α	4.06	4.83	0.160	0.190	
A1	0.00	0.254	0.000	0.010	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
Н	14.61	15.88	0.575	0.625	
L	1.78	2.79	0.070	0.110	
L1	-	1.65	1	0.066	3
L2	1.27	1.78	0.050	0.070	
L3	0.25 BSC		0.010 BSC		
L4	4.78	5.28	0.188	0.208	

Notes

- $^{(1)}$ Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC outline TO-263AB



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Revision: 02-Oct-12 Document Number: 91000